



ITW

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Patent Application of

CHO ET AL.

Atty. Ref.: 4105-73; Confirmation No. 6675

Appl. No. 10/568,770

TC/A.U. 1792

Filed: February 21, 2006

Examiner: George

For: FERROELECTRIC THIN-FILM PRODUCTION METHOD, VOLTAGE-APPLICATION  
ETCHING APPARATUS, FERROELECTRIC CRYSTAL THIN-FILM SUBSTRATE,  
AND FERROELECTRIC CRYSTAL WAFER

\* \* \* \* \*

February 13, 2008

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Sir:

**RESPONSE TO REQUIREMENT FOR RESTRICTION**

Responsive to the Official Action of January 25, 2008 and the requirement for restriction presented in it, applicant elects the subject matter of claims 1-20, Group I, directed to a method. This response is made without traverse.

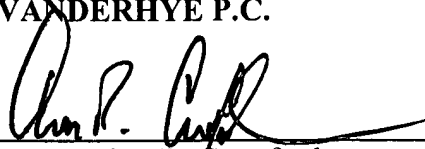
Please examine the elected claims on the merits taking into account the documents cited in the International Search Report in the underlying PCT application and the Information Disclosure Statement filed February 21, 2006.

CHO ET AL.  
Appl. No. 10/568,770  
February 13, 2008

Respectfully submitted,

**NIXON & VANDERHYE P.C.**

By: \_\_\_\_\_



Arthur R. Crawford  
Reg. No. 25,327

ARC:eaw  
901 North Glebe Road, 11th Floor  
Arlington, VA 22203-1808  
Telephone: (703) 816-4000  
Facsimile: (703) 816-4100